

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#8
607 (2m) A F
5 Derine
6/12/03

in re the Application of: KANO, Takashi et al.

Group Art Unit: 2812

Serial No.: 09/941,982

Examiner: MULPURI, Savitri

Filed: August 30, 2001

P.T.O. Confirmation No.: 7536

For.

METHOD OF FORMING NITRIDE-BASED SEMICONDUCTOR LAYER, AND METHOD OF MANUFACTURING NITRIDE-BASED SEMICONDUCTOR

**DEVICE** 

## **PETITION FOR EXTENSION OF TIME**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Date: June 9, 2003

Sir:

Applicants petition the Commissioner for Patents to extend the time for response to the Office Action dated January 8, 2003 for two months from April 8, 2003 to June 8, 2003.

Attached please find a check in the amount of \$410.00 to cover the cost of the extension for a large entity. In the event that any additional fees are due in connection with this paper, please charge our Deposit Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP

06/10/2003 CNGUYEN 00000108 09941982

01 FC:1252

410.00 OP

Stephen G. Adrián Attorney for Applicant Reg. No. 32,878

SGA/nrp Atty. Docket No. **011083** Suite 1000 1725 K Street, N.W. Washington, D.C. 20006 (202) 659-2930

23850

PATENT TRADEMARK OFFICE